

## N-Channel 100 V (D-S) MOSFET

### PRODUCT SUMMARY

V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a, e</sup>	Q <sub>g</sub> (Typ.)
100	0.011 at V <sub>GS</sub> = 10 V	48	15 nC
	0.015 at V <sub>GS</sub> = 4.5 V	40	

### FEATURES

- DT-Trench Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested

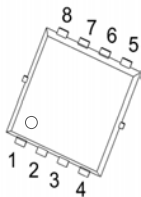


### APPLICATIONS

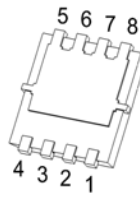
- Notebook PC Core
- VRM/POL

PDFN 3.3x3.3

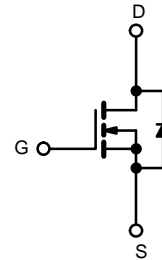
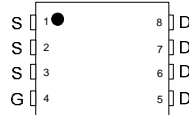
Top View



Bottom View



Top View



N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	100	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 175 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	48 <sup>a, e</sup>	A
		T <sub>C</sub> = 70 °C	30 <sup>e</sup>	
Pulsed Drain Current	I <sub>DM</sub>	192		
Avalanche Current Pulse	I <sub>AS</sub>	48		
Single Pulse Avalanche Energy	E <sub>AS</sub>	53	mJ	
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	45 <sup>a, e</sup>	A
		T <sub>C</sub> = 70 °C		
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	52	W
		T <sub>C</sub> = 70 °C	33.3	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C	

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	R <sub>thJA</sub>	40	62	°C/W
Maximum Junction-to-Case	R <sub>thJC</sub>	1.5	2.5	

Notes:

a. Based on T<sub>C</sub> = 25 °C.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 10 s.

d. Maximum under steady state conditions is 90 °C/W.

e. Calculated based on maximum junction temperature. Package limitation current is 80 A.

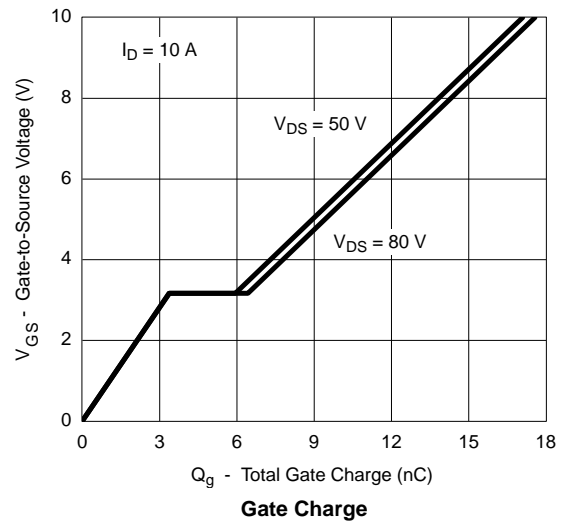
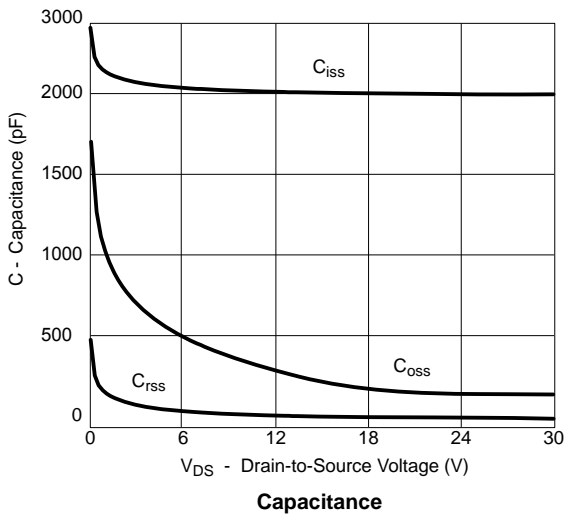
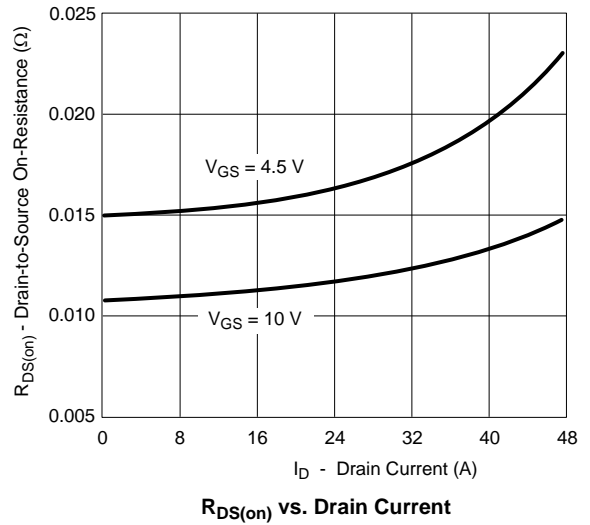
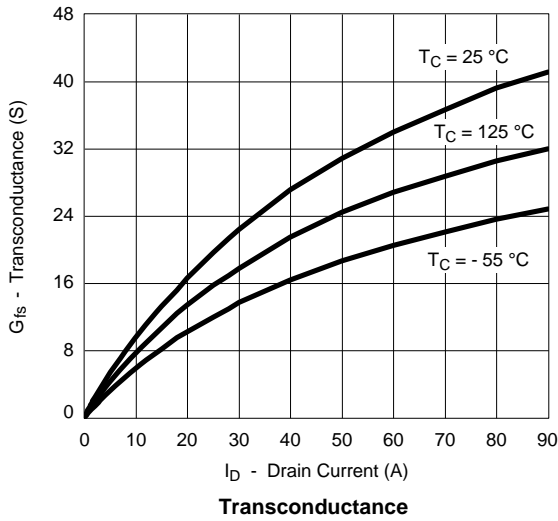
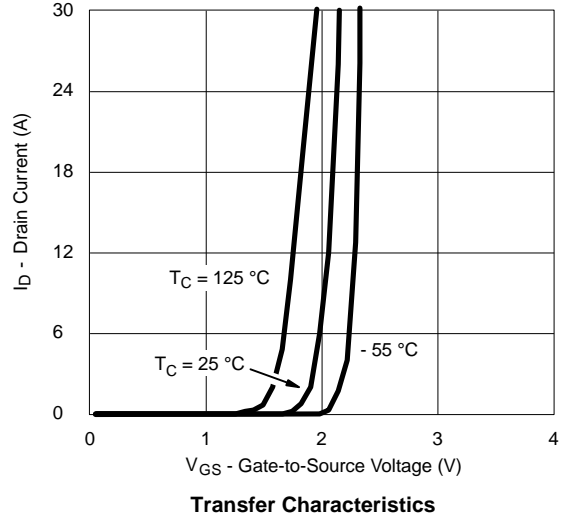
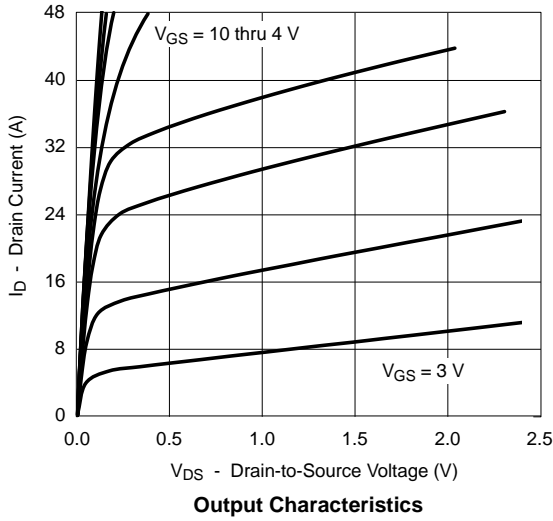
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min .	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	100			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		35		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 5.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0		3.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	45			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$		0.011	0.015	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 8\text{ A}$		0.015	0.023	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 10\text{ A}$		15		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		2016		pF
Output Capacitance	$C_{oss}$			198		
Reverse Transfer Capacitance	$C_{rss}$			56		
Total Gate Charge	$Q_g$	$V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 10\text{ A}$		15		nC
				11		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 50\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 8\text{ A}$		6		
Gate-Drain Charge	$Q_{gd}$			4		
Gate Resistance	$R_g$		$f = 1\text{ MHz}$		1.4	2.0
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 50\text{ V}, R_L = 0.555\text{ }\Omega$ $I_D \cong 7\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		18		ns
Rise Time	$t_r$			21		
Turn-Off Delay Time	$t_{d(off)}$			50		
Fall Time	$t_f$			30		
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			48	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				192	
Body Diode Voltage	$V_{SD}$	$I_S = 1\text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		52		ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			75		nC
Reverse Recovery Fall Time	$t_a$			27		ns
Reverse Recovery Rise Time	$t_b$			25		

**Notes:**

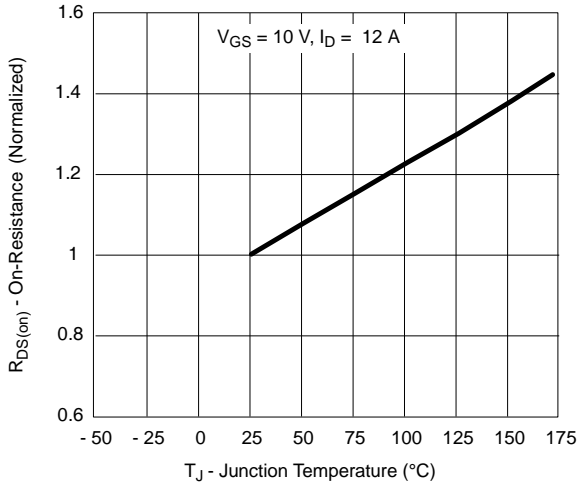
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



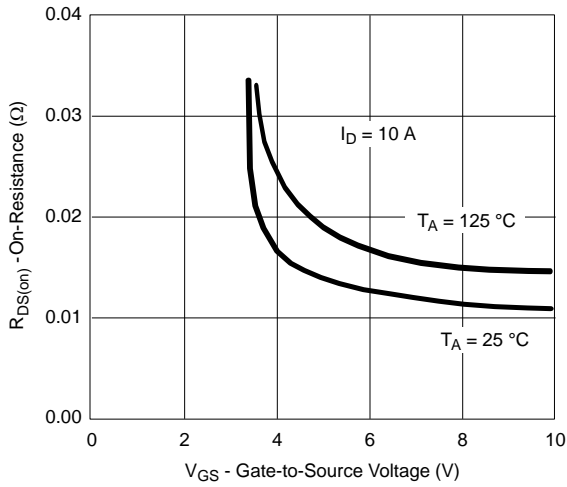
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



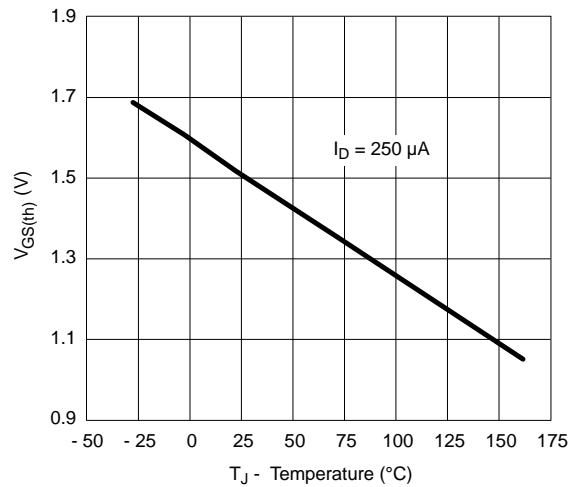
**On-Resistance vs. Junction Temperature**



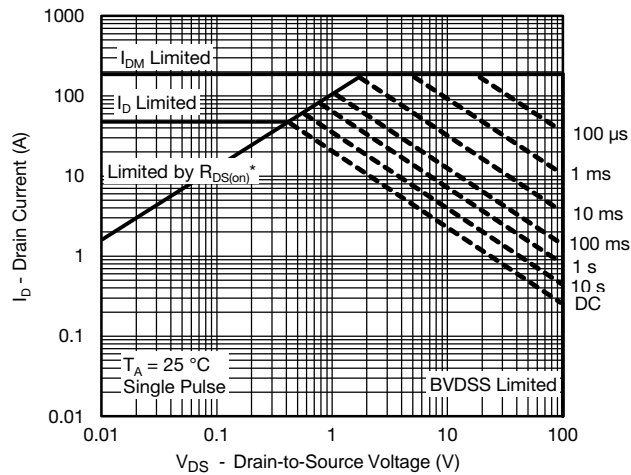
**Forward Diode Voltage vs. Temperature**



**R<sub>DS(on)</sub> vs. V<sub>GS</sub> vs. Temperature**

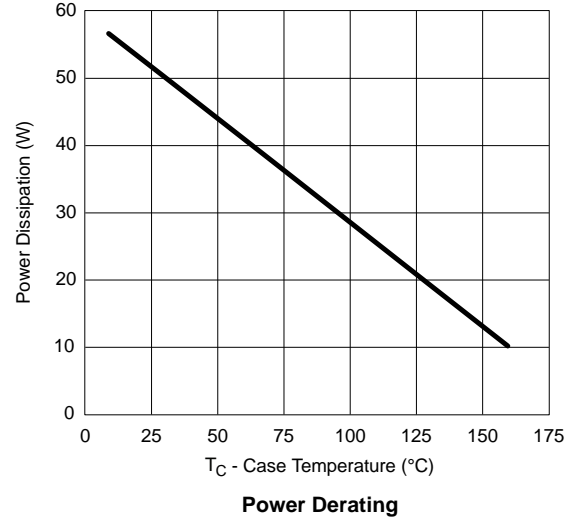
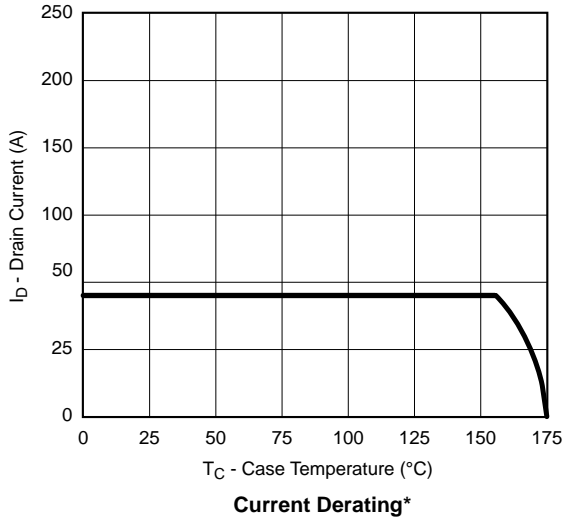


**Threshold Voltage**

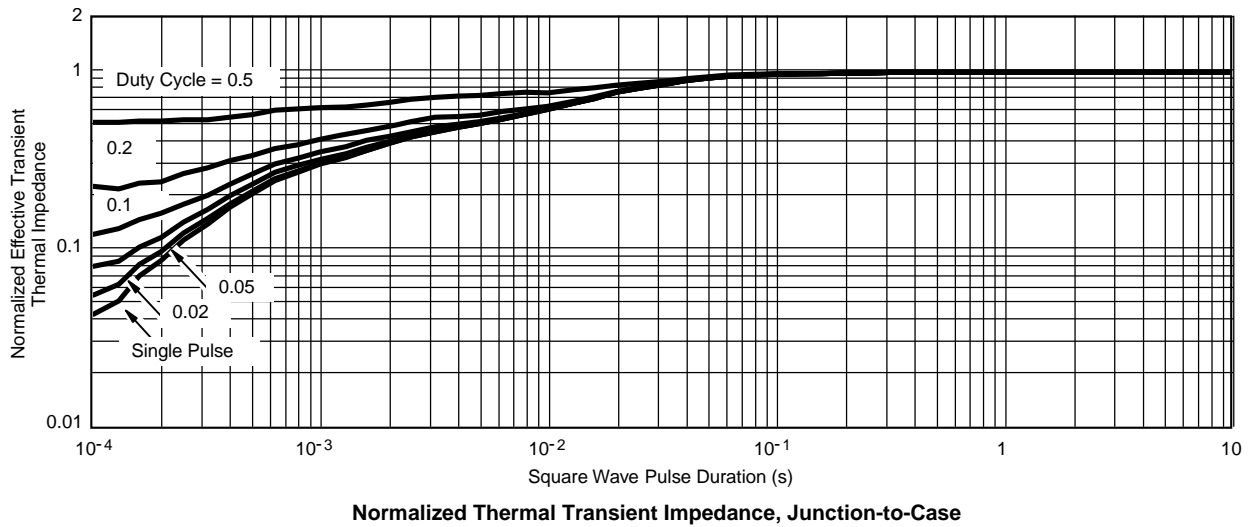


**Safe Operating Area, Junction-to-Ambient**

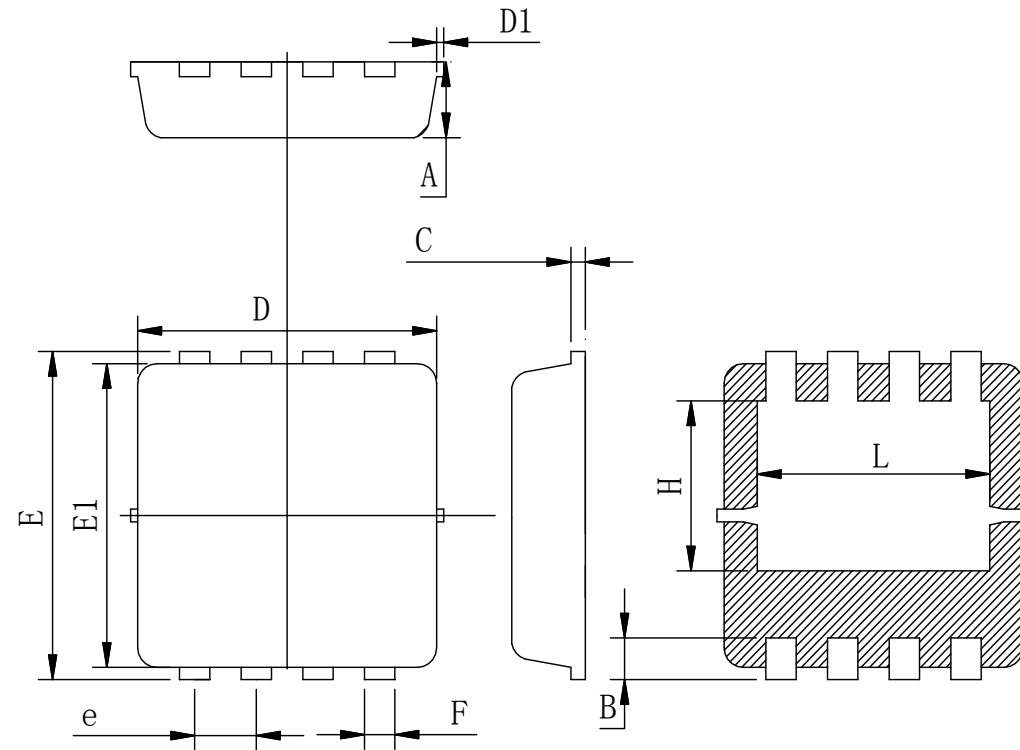
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 175$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



## PDFN 3.3X3.3 PACKAGE OUTLINE



COMMON DIMENSIONS  
(UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Typ	Max
A	0.600	0.775	1.000
B	0.20	0.38	0.55
C	0.05	0.15	0.40
D	3.10	3.25	3.50
D1	-	-	0.15
E	3.15	3.35	3.50
E1	2.60	3.10	3.45
e	0.50	0.65	0.80
F	0.15	0.32	0.45
H	1.25	1.73	2.10
L	2.20	2.45	2.85

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